VE320 – Summer 2021

Introduction to Semiconductor Devices

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Chapter 12 Bipolar Junction Transistor

Outline

12.1 Review and example

12.2 Bipolar Junction transistor

12.3 Early Effect

12.4 Summary

12.5 Quantitative analysis of BJT gain

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12.1 Review and example

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12.1 Previously: pn Junction Current

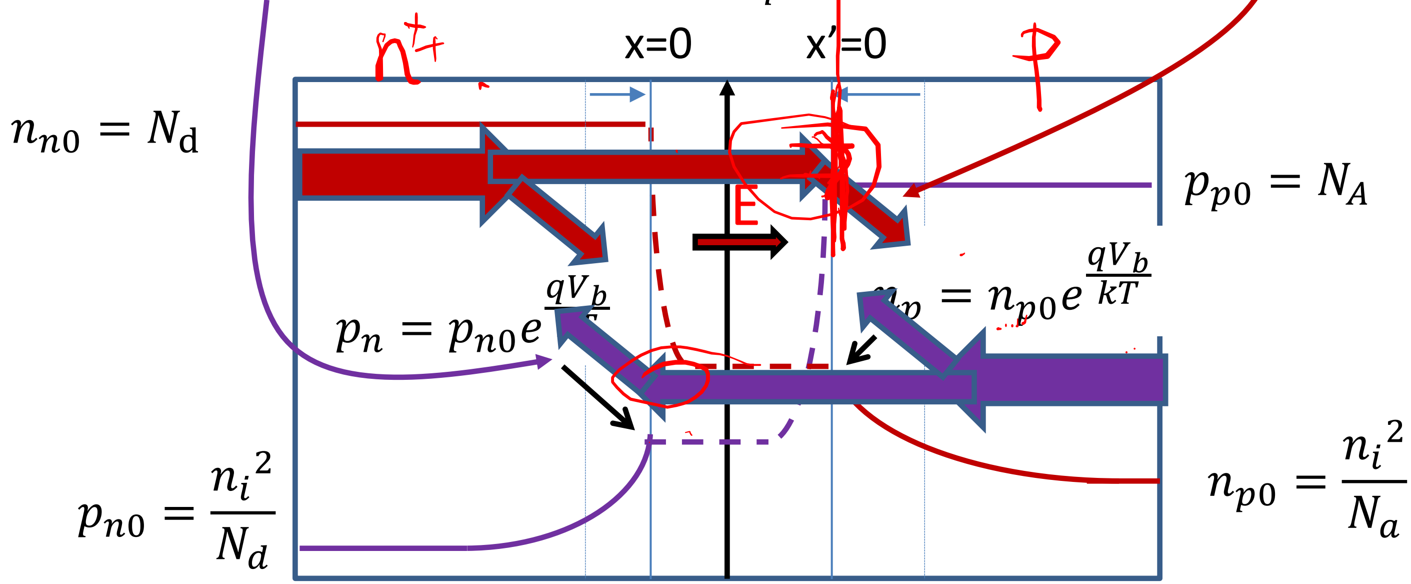
- charge carrier transport: forward bias: current ratio

$$J_n = -qD_n\frac{dn_p}{dx} = -\frac{qD_n n_{p0}}{L_n}\left(e^{\frac{qV_b}{kT}} - 1\right)e^{-x/L_n}$$

$$J_p = -qD_p\frac{dp_n}{dx} = -\frac{qD_p p_{n0}}{L_p}\left(e^{\frac{qV_b}{kT}} - 1\right)e^{x/L_p}$$

$x'=0$

$$\boxed{\frac{J_n}{J_p} = \frac{D_n N_d/L_n}{D_p N_a/L_p}}$$



Assumption: No recombination-generation in depletion region.

12.1 Example: pn Junction Current

Finding L_n, τ_n in **p-type** region because electrons are minority carriers.

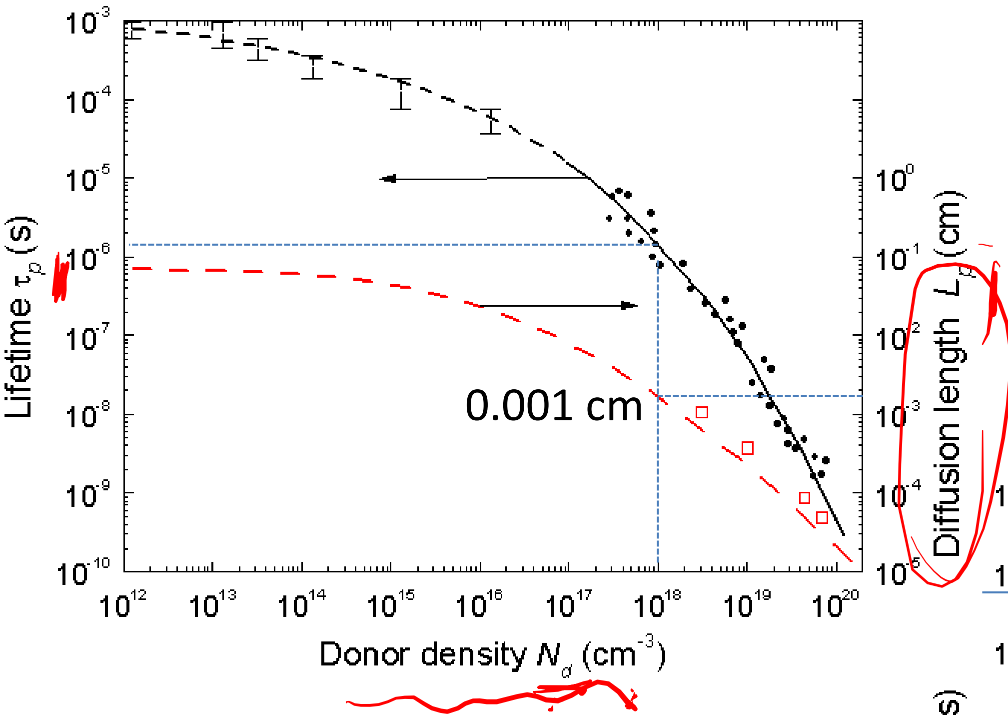
For $N_a = 10^{16}\ cm^{-3}$ $\quad L_n = 0.04cm \quad \tau_n = 5 \times 10^{-5} s$

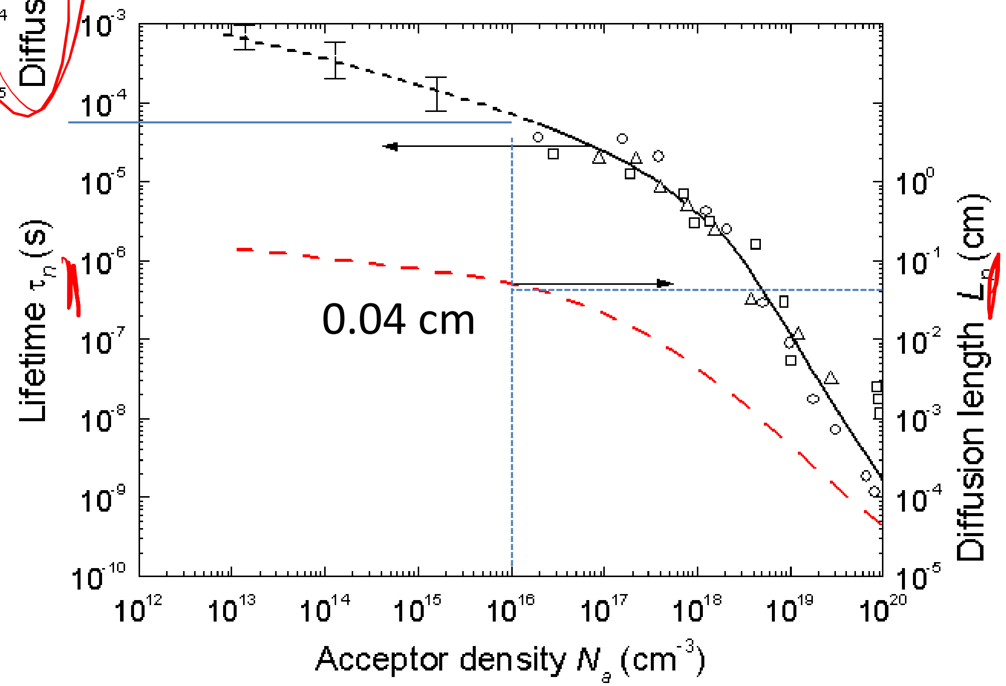
Finding L_p, τ_p in **n-type** region because holes are minority carriers.

For $N_d = 10^{18}\ cm^{-3}$ $\quad L_p = 0.0015cm \quad \tau_p = 1.5 \times 10^{-6} s$

$$\frac{J_n}{J_p} = \frac{D_n N_d / L_n}{D_p N_a / L_p} = \frac{L_n/\tau_n}{L_p/\tau_p}\frac{N_d}{N_a} \approx \frac{\frac{4 \times 10^{-2}}{5 \times 10^{-5}}}{\frac{1.5 \times 10^{-3}}{1.5 \times 10^{-6}}} \times \frac{10^{18}}{10^{16}} = 80$$

12.1 Example: pn Junction Current





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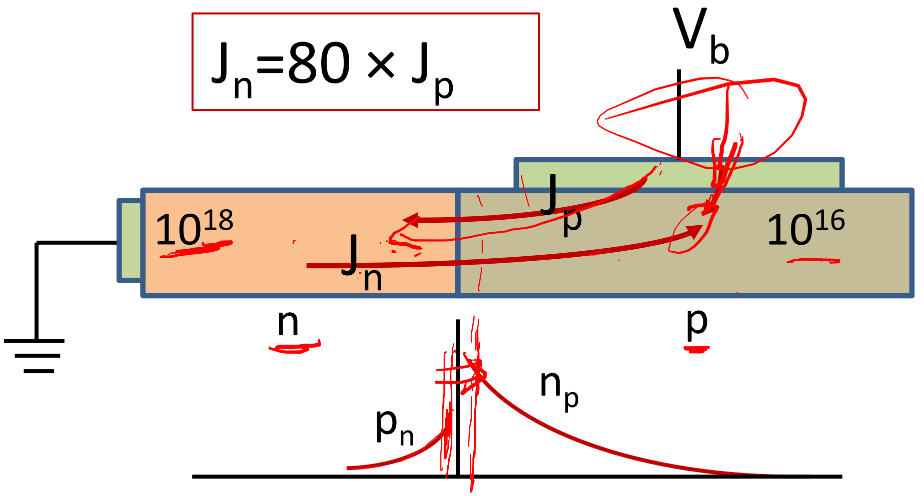
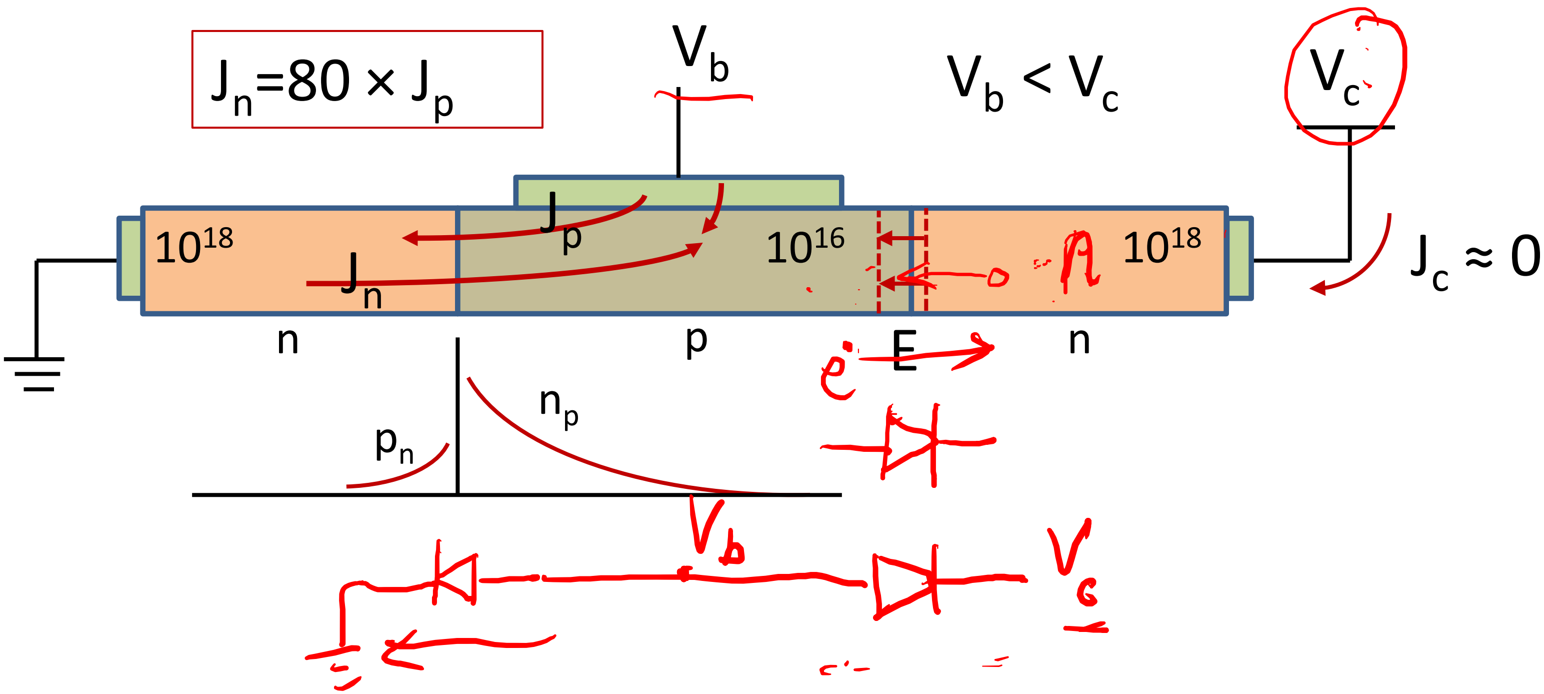
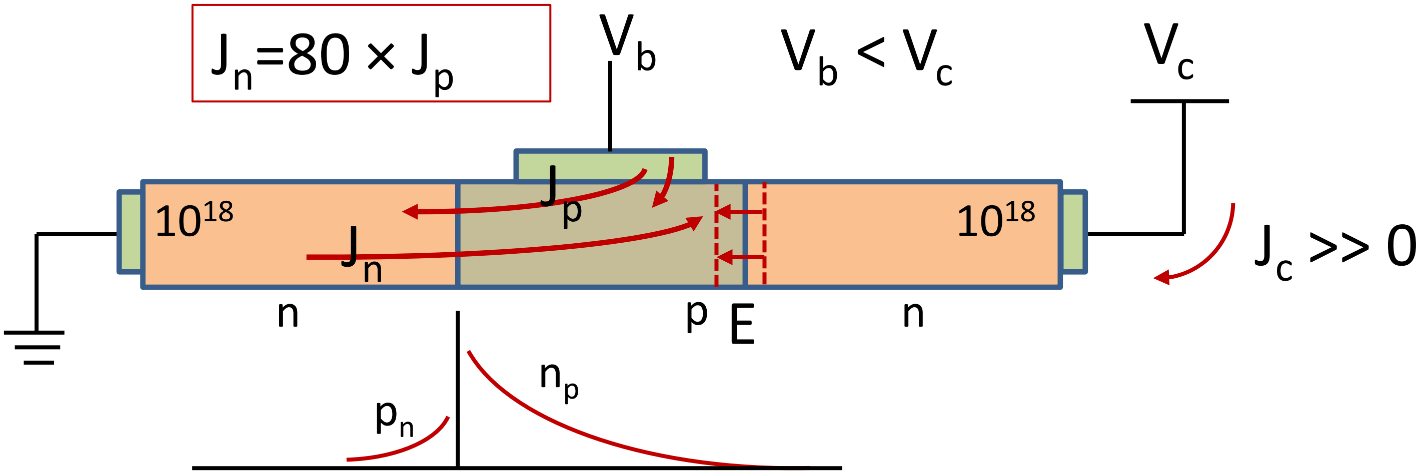
12.2 Bipolar Junction transistor



12.2 Bipolar Junction transistor



12.2 Bipolar Junction transistor



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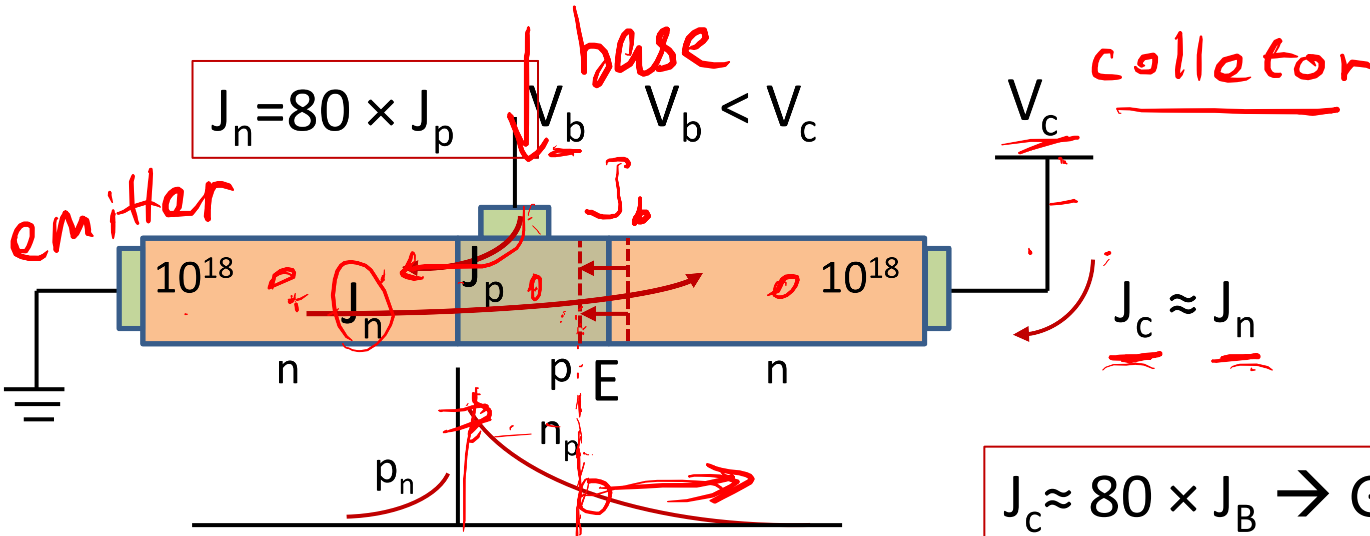
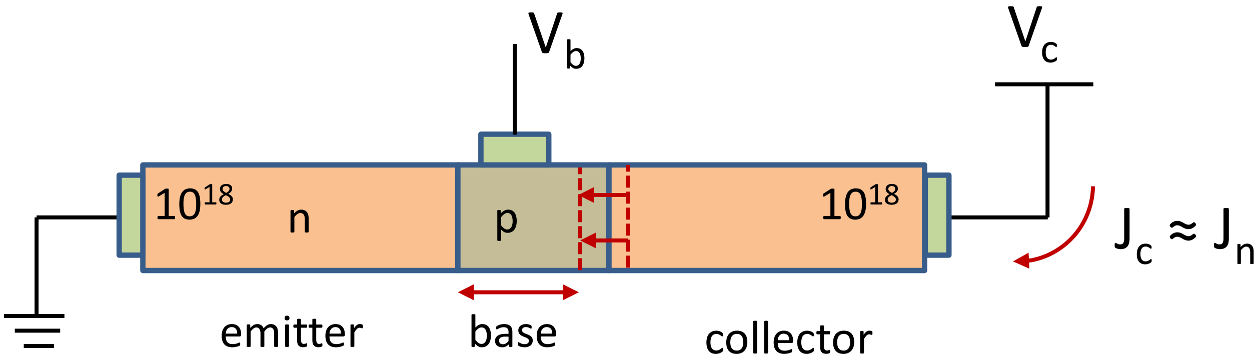


$J_c \approx 80 \times J_B \rightarrow$ Gain $\beta=80$

$J_B \approx J_p$

12.2 Bipolar Junction transistor

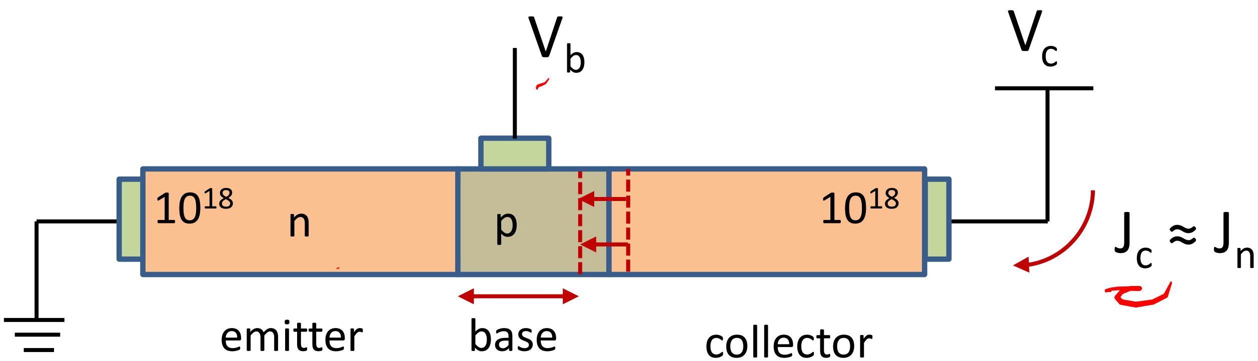


$$\boxed{J_c \approx 80 \times J_B \rightarrow \text{Gain } \beta=80}$$

BJT Charateristics:

1. Base width smaller → higher gain
2. Larger emitter-base concentration ratio → higher gain

12.2 Bipolar Junction transistor: I-V



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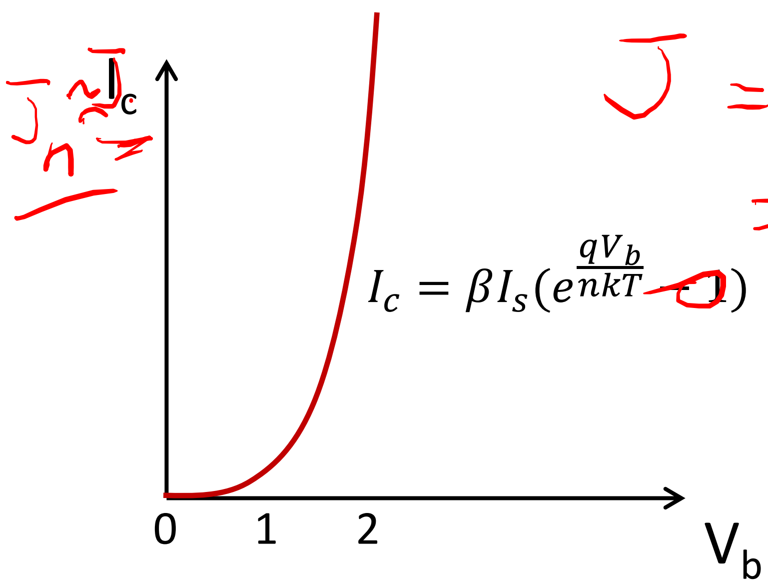
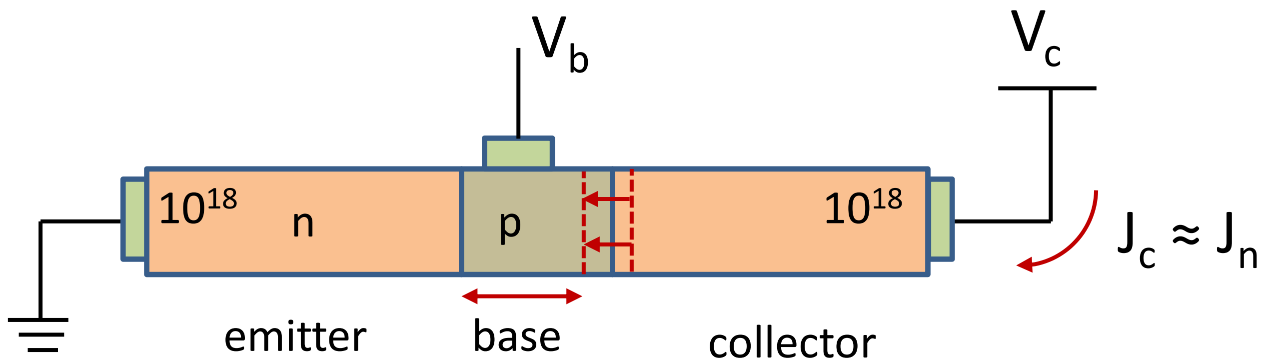


$$J = J_s\left(\exp\left(\frac{qV_b}{kT}\right) - 1\right)$$

$$= \left(\frac{D_n \cdot n_{p0}}{L_n} + \frac{D_p \cdot p_{n0}}{L_p}\right) e^{\frac{qV_b}{kT}}$$

$$= \underbrace{\frac{D_n n_{p0}}{L_n} e^{\frac{qV_b}{kT}}}_{J_n} + \underbrace{\frac{D_p p_{n0}}{L_p} e^{\frac{qV_b}{kT}}}_{J_p}$$

12.2 Bipolar Junction transistor: I-V



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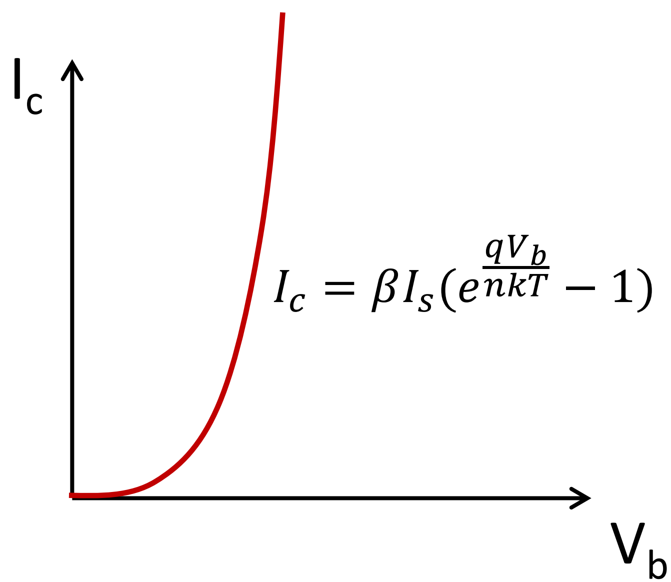

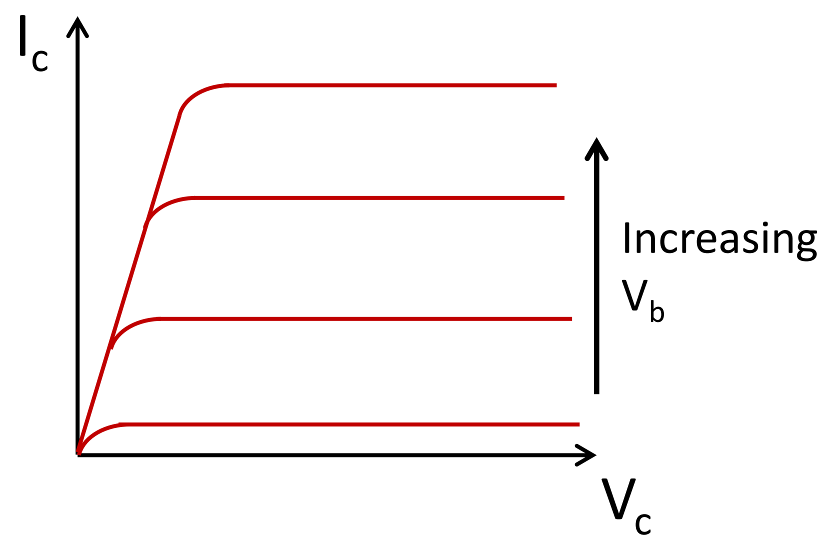

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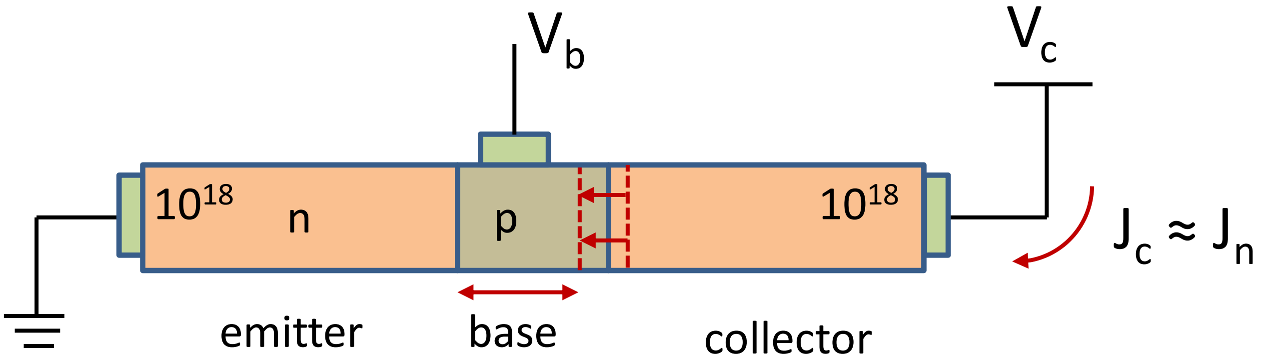

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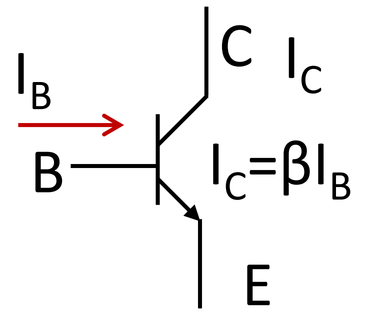
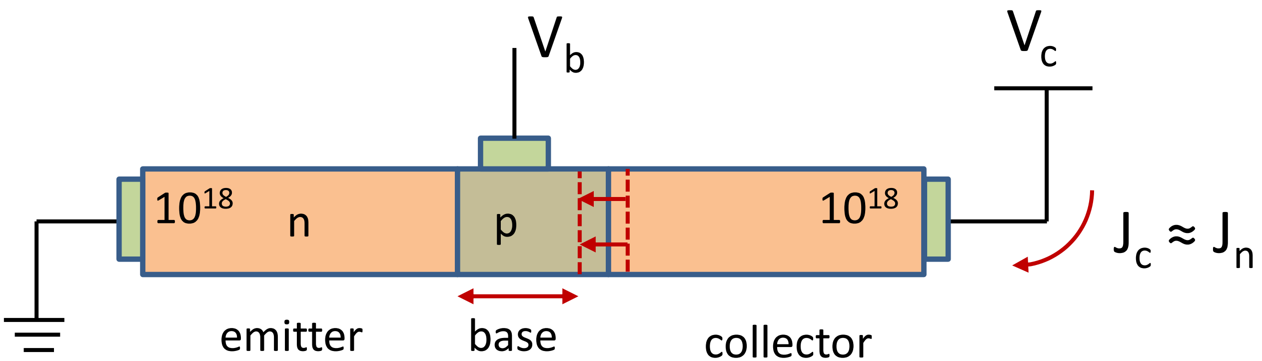
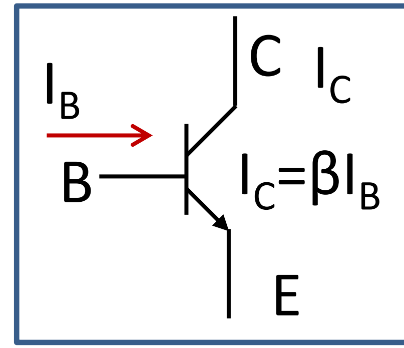


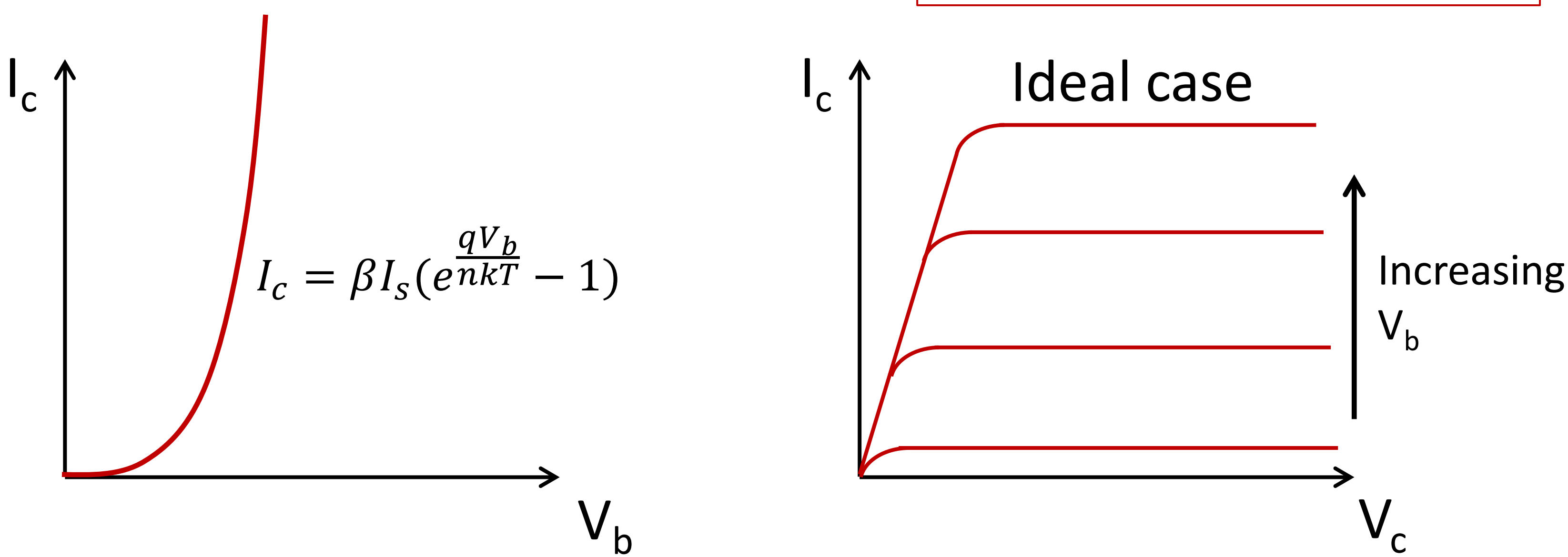
Basic facts:

12.2 Bipolar Junction transistor: I-V



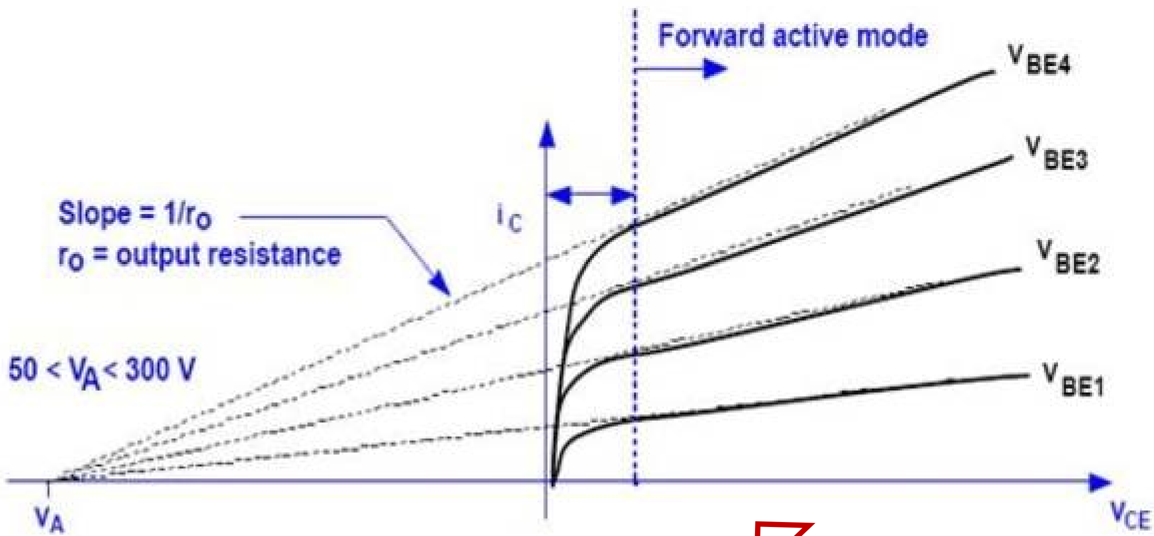


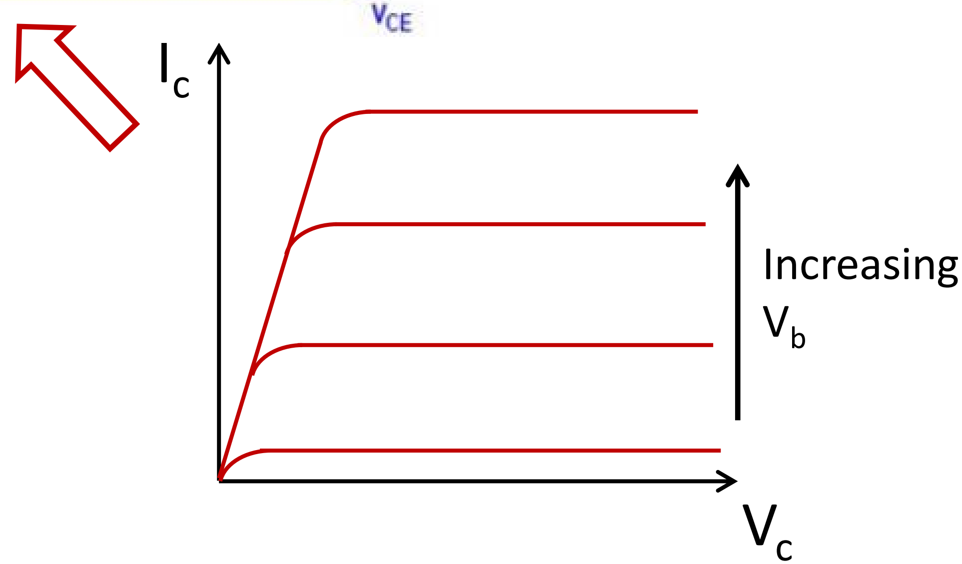
$J_c \approx 80 \times J_B \rightarrow$ Gain β=80



Outline

12.3 Early Effect





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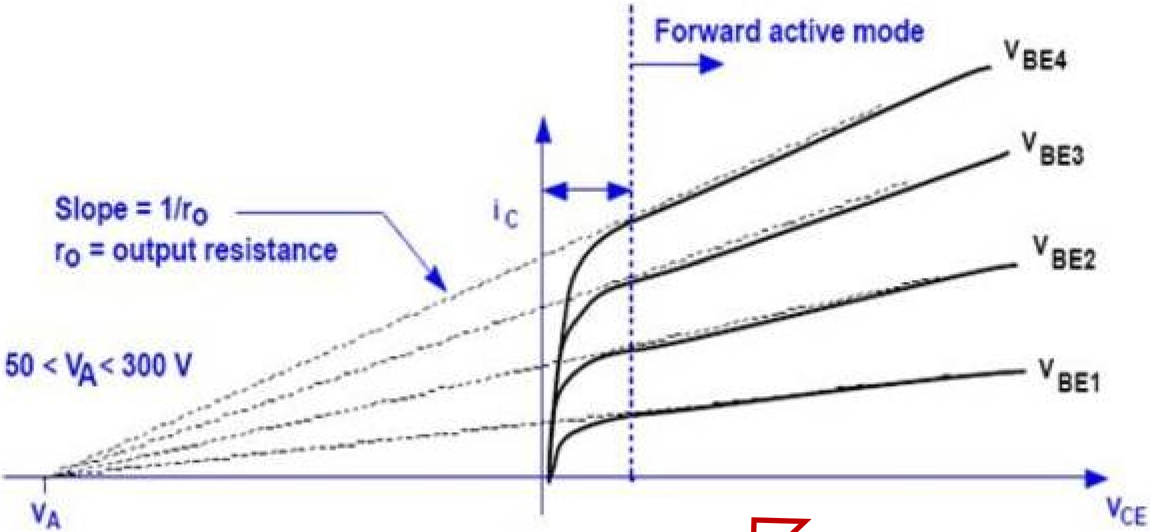
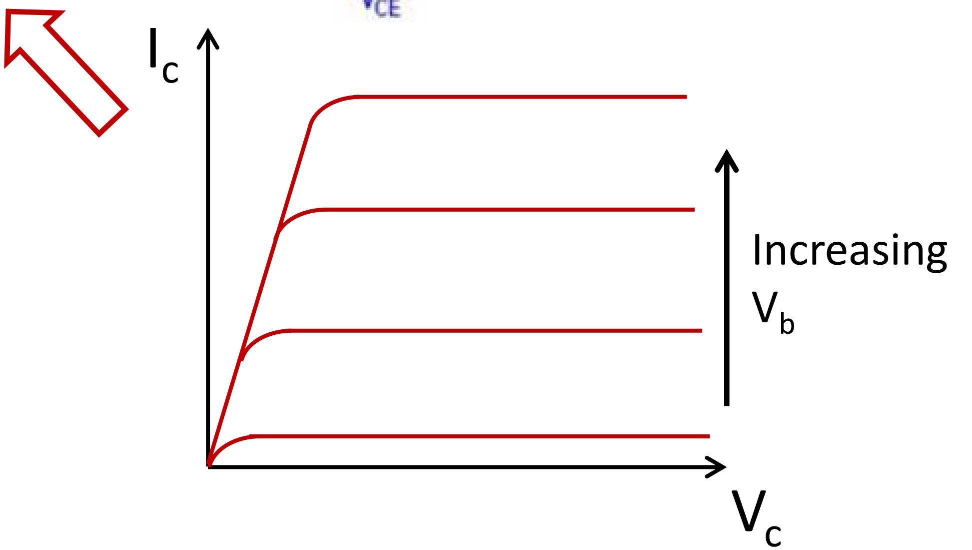


[James M. Early]()



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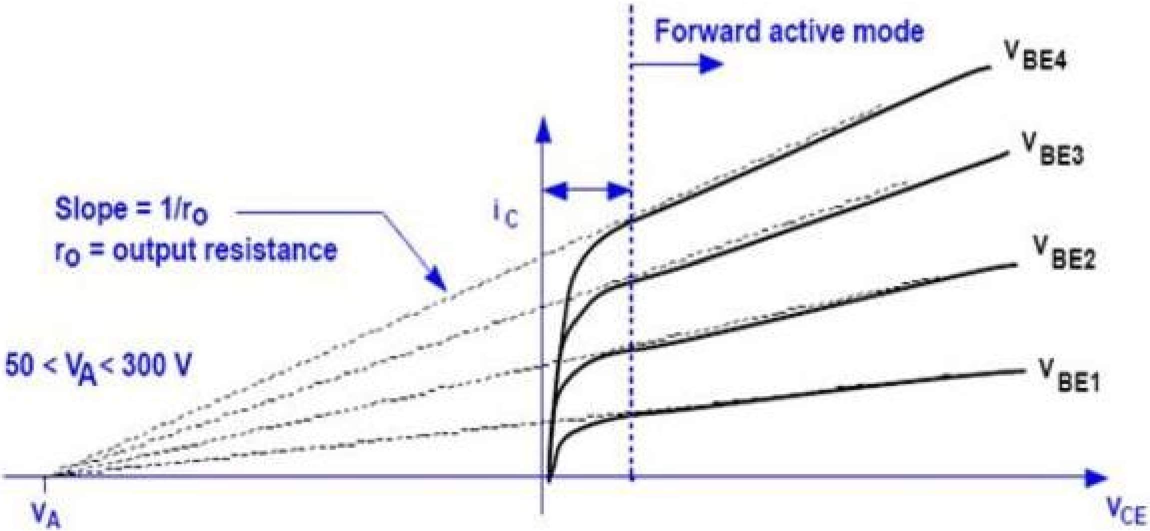

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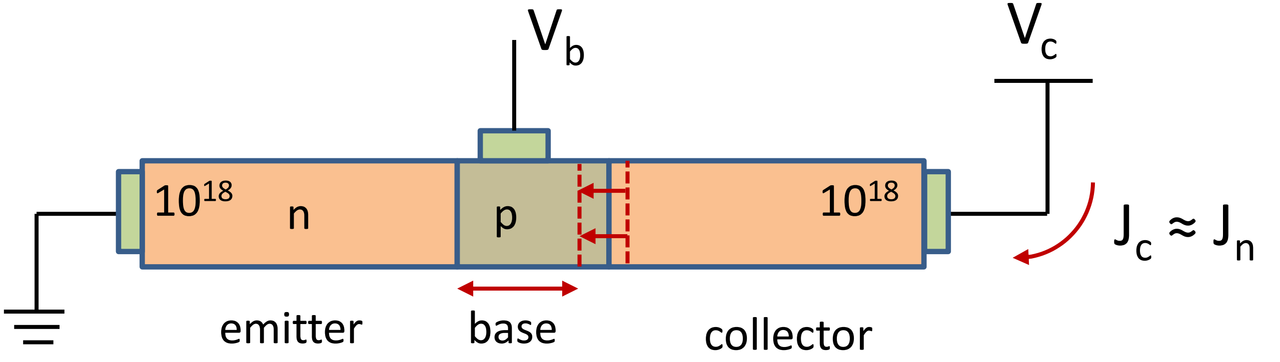

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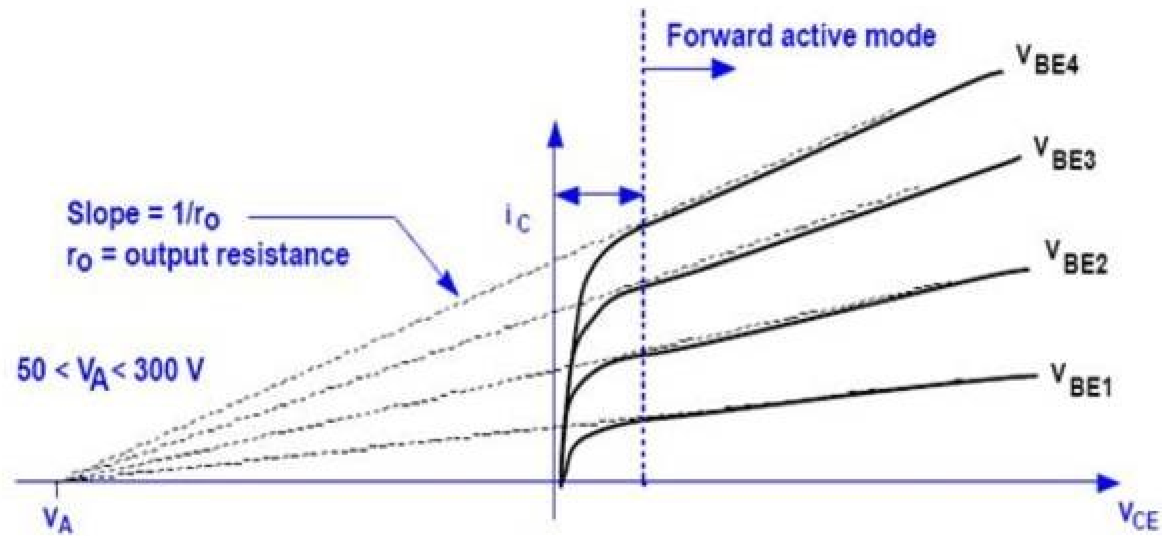

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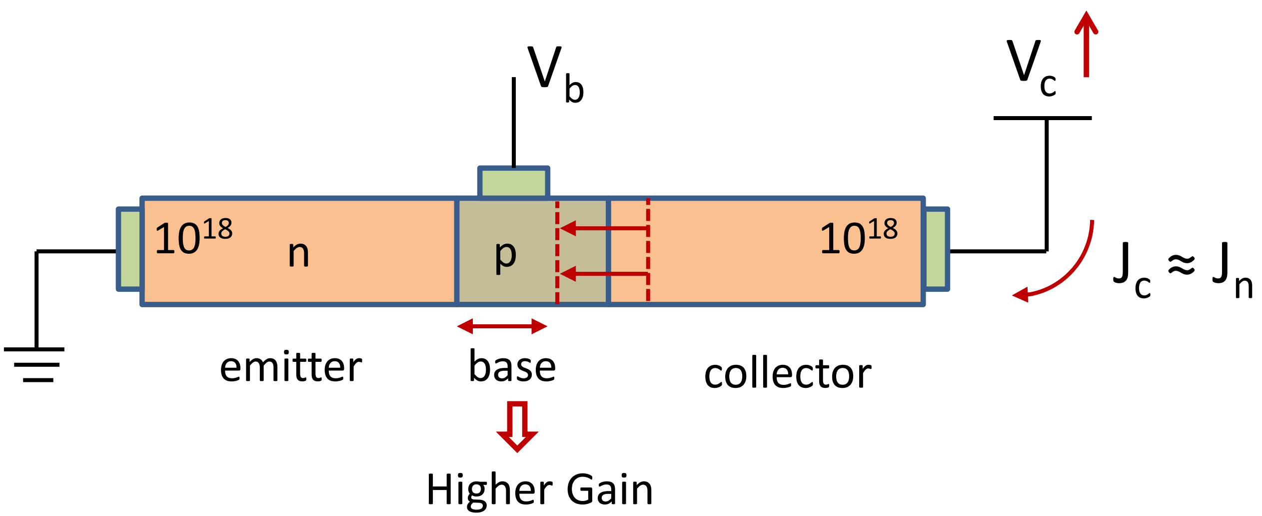
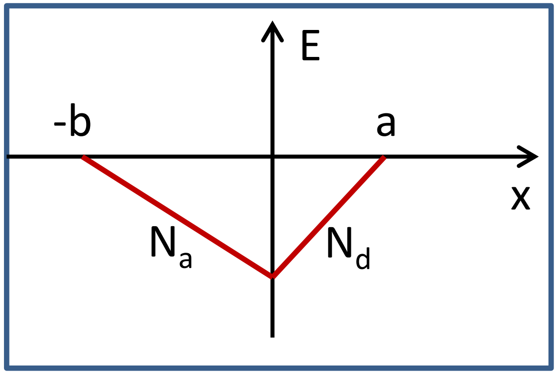
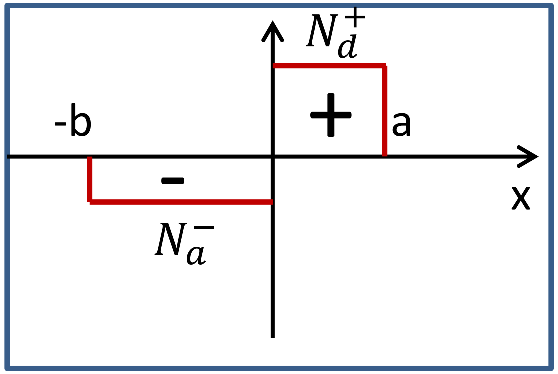


Previously…

$$a = \sqrt{\frac{2\varepsilon(V_{bi}-V_R)}{q}\frac{N_a}{N_d}\frac{1}{N_a+N_d}}$$

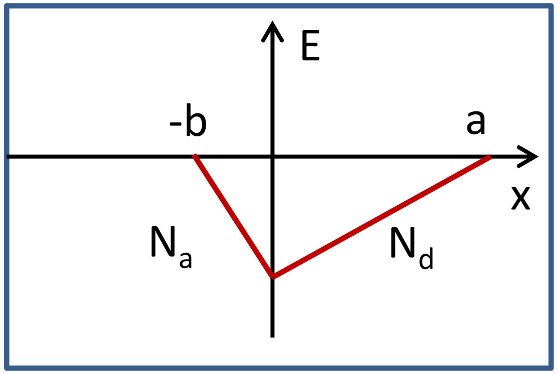
$$N_A^- b = N_D^+ a \Rightarrow b = \sqrt{\frac{2\varepsilon(V_{bi}-V_R)}{q}\frac{N_d}{N_a}\frac{1}{N_a+N_d}}$$

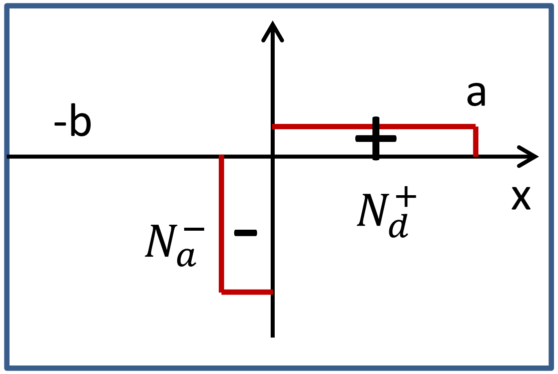




Previously…

Depletion region width W = a + b





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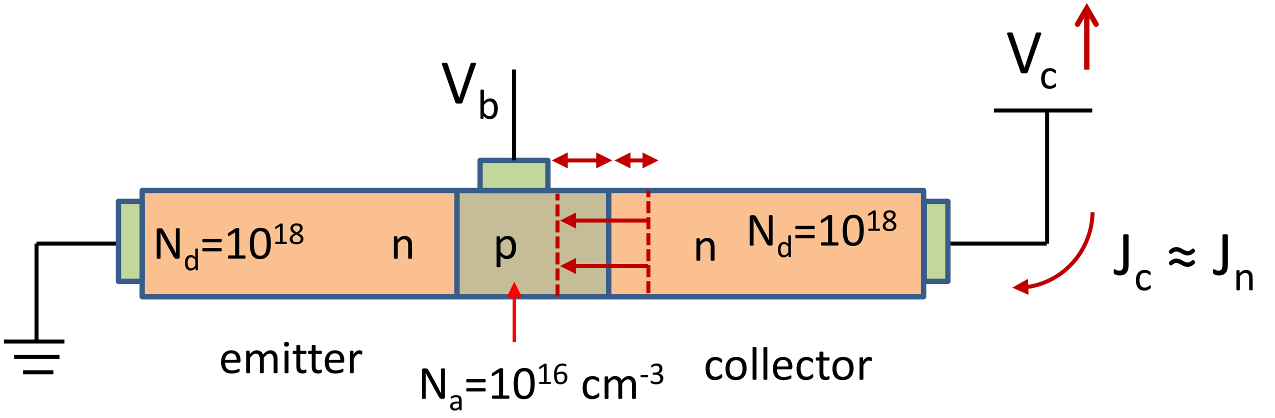

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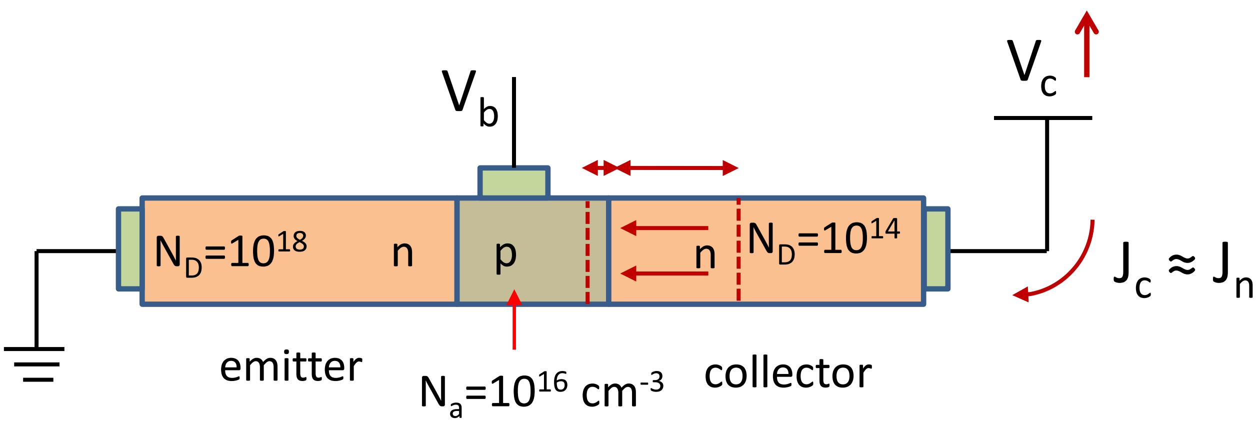
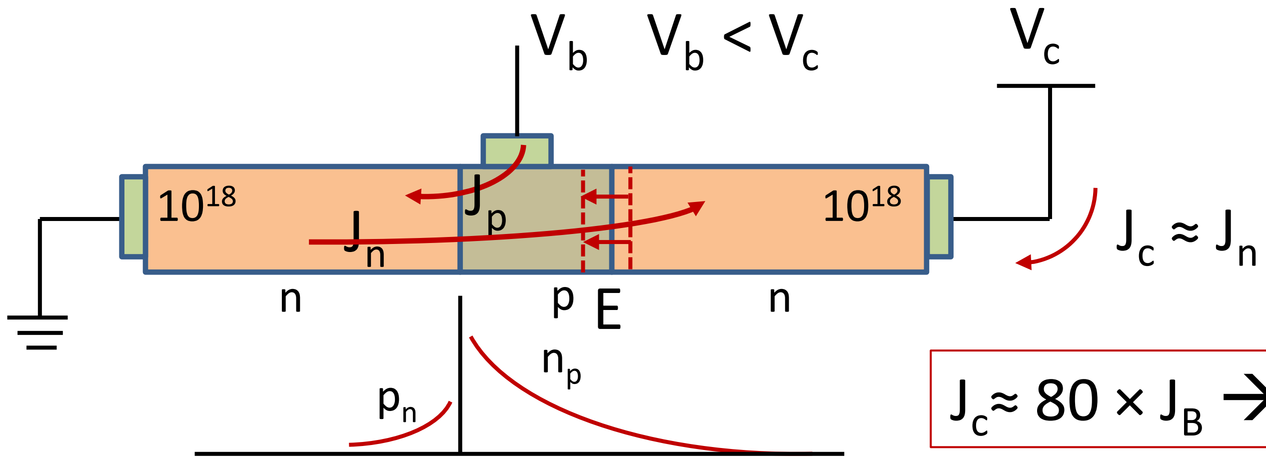


12.3 Early Effect

Outline

12.4 Summary



$J_c \approx 80 \times J_B \rightarrow$ Gain β=80

1. highest doping concentration is limited by solubility ($<10^{20}$)
2. Lowest doping concentration is limited by n_i and fabrication process

Basic facts:

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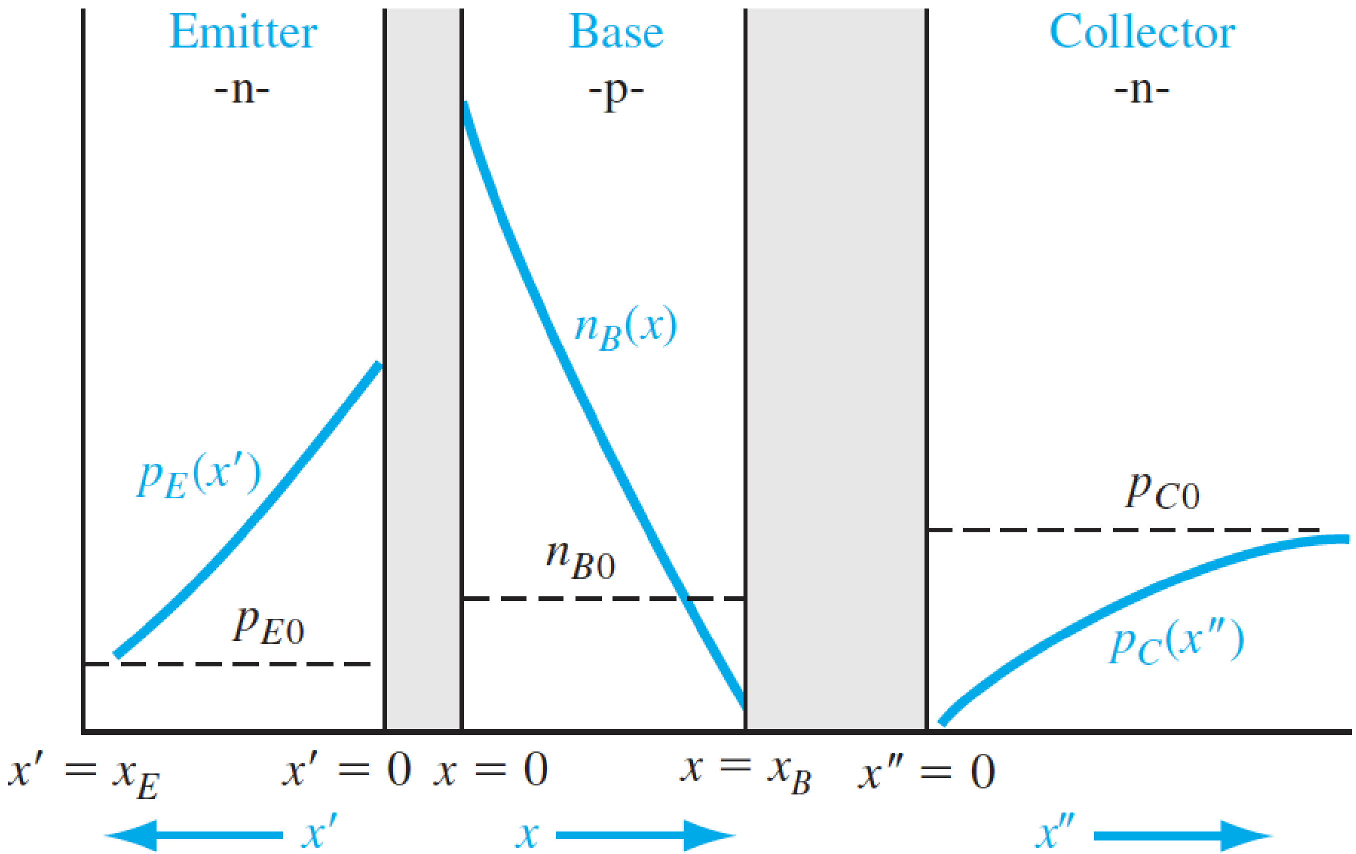
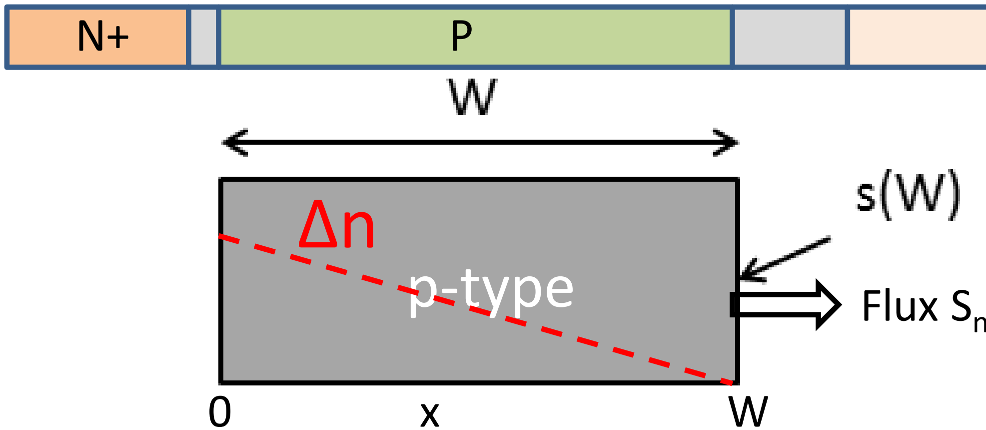


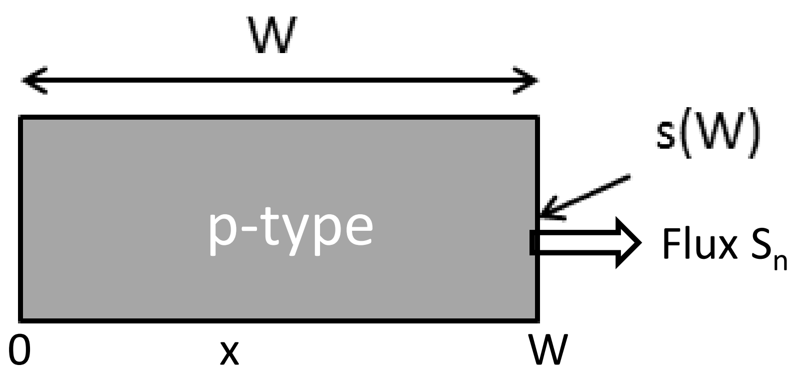
12.5 Quantitative analysis of BJT gain



$N_a = 10^{17}$ cm^{-3}, $D_n = 10$ cm^2/s, $\tau_n = 10^{-7}$ s, SRV $s(x{=}W) = \infty$
$\Delta n\ (x{=}0) = 10^{14}$ cm^{-3}

Find the electron flux Sn at x=0 and W, if
1) W=20um
2) W=2um

12.5 Quantitative analysis of BJT gain



$$\boxed{0 = D_n \frac{\partial^2 \Delta n}{\partial x^2} - \frac{\Delta n}{\tau}}$$

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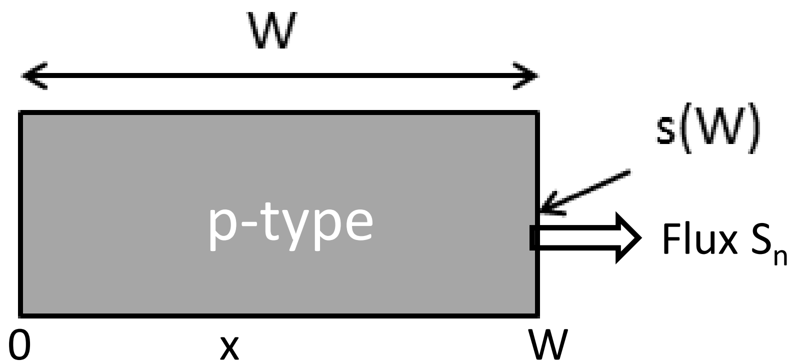

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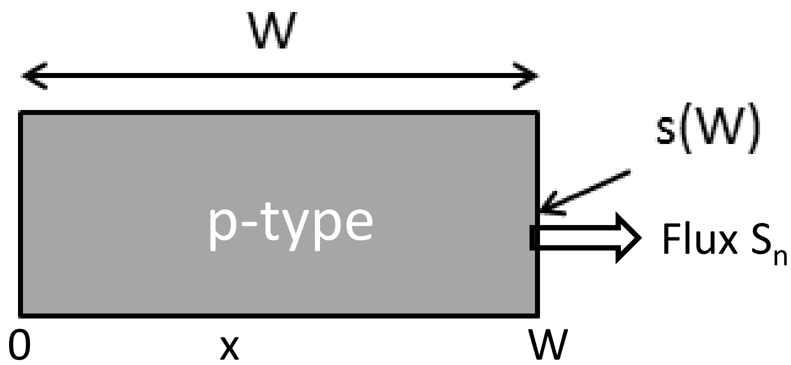

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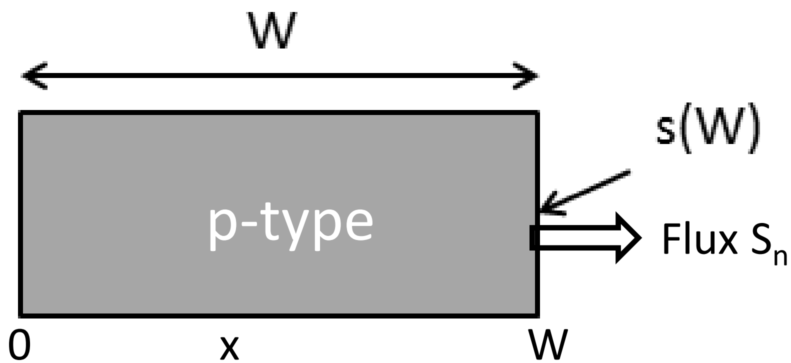

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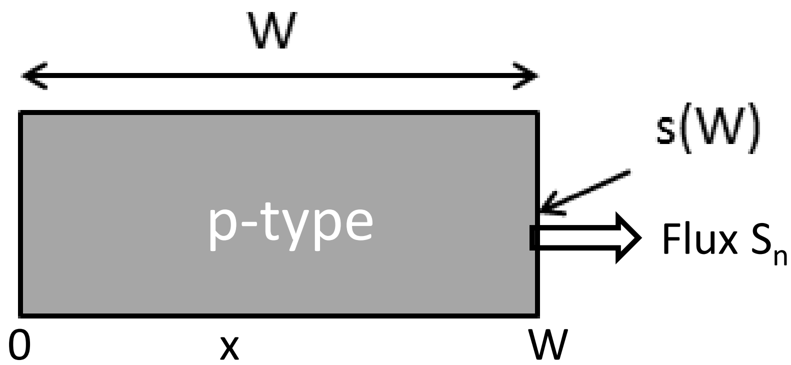

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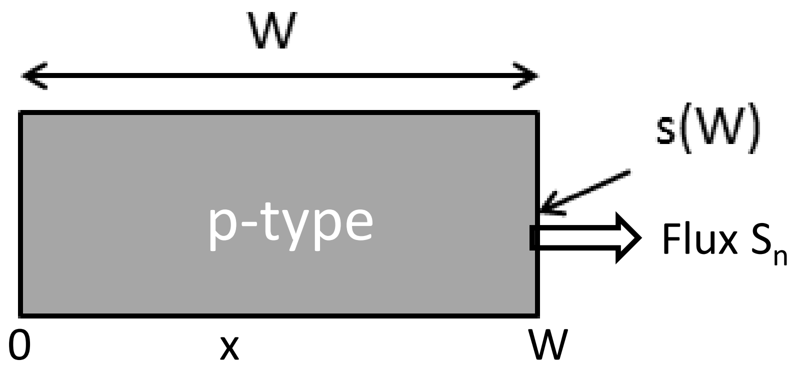

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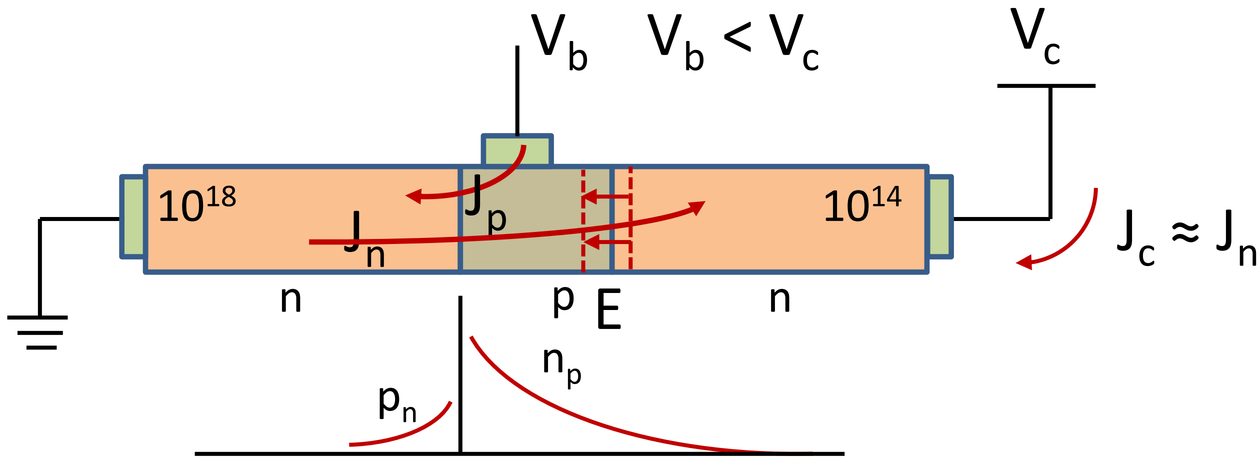
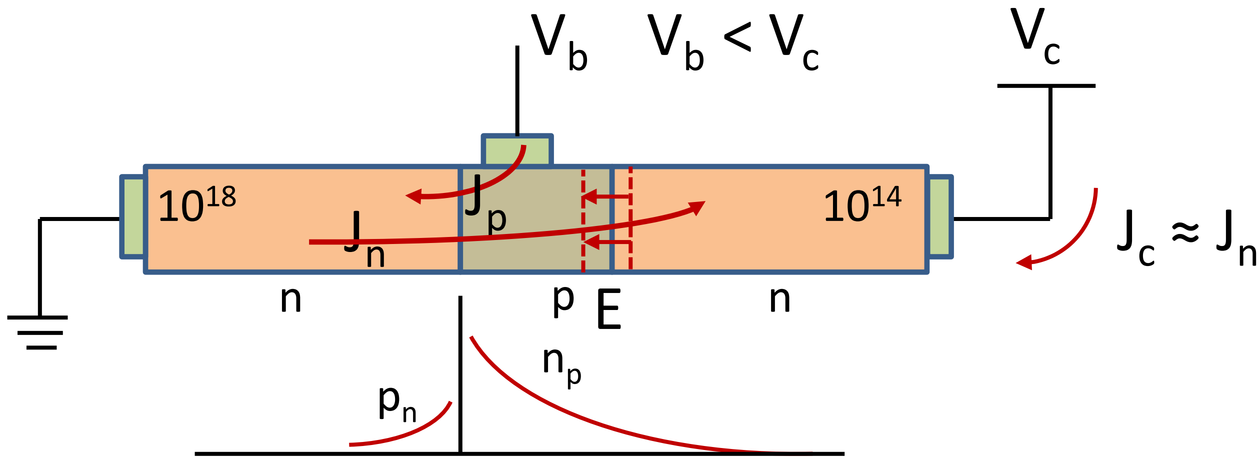


Electron flux from emitter to base: $S_n(0)$
Electron flux from base to collector: $S_n(W_b)$

12.5 Quantitative analysis of BJT gain



Electron flux from emitter to base: $S_n(0)$
Electron flux from base to collector: $S_n(W_b)$
Hole flux from base to emitter: S_p

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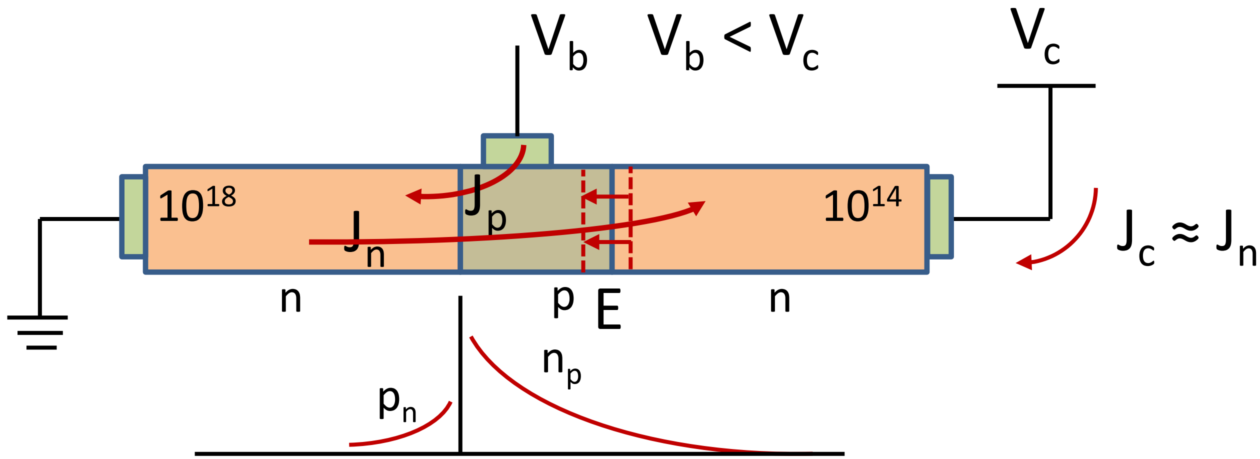

Electron flux from emitter to base: $S_n(0)$

Electron flux from base to collector: $S_n(W_b)$

Hole flux from base to emitter: S_p

Base electrode flux: $S_p + S_n(0)\text{-}S_n(W_b)$

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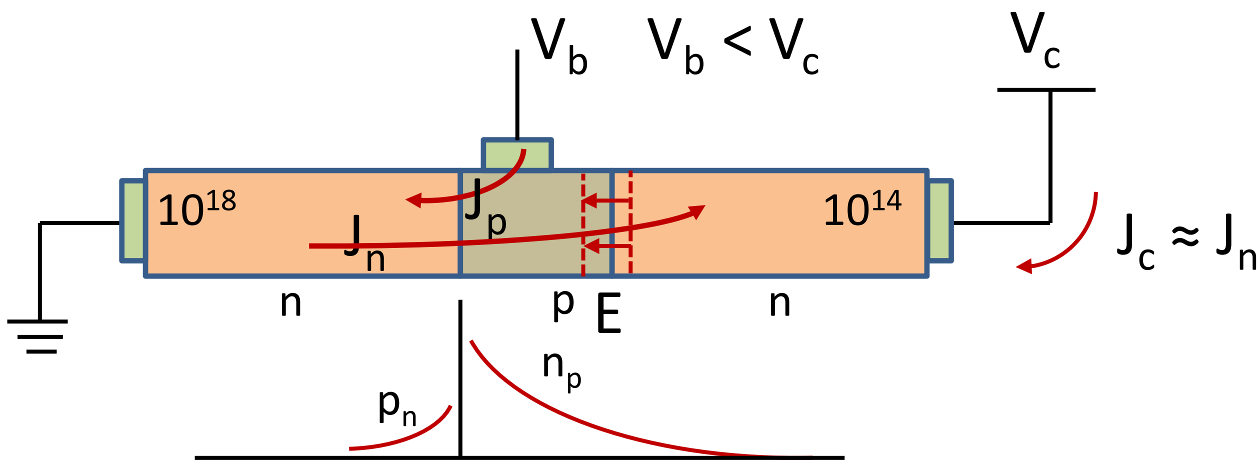

Electron flux from emitter to base: $S_n(0)$
Electron flux from base to collector: $S_n(W_b)$
Hole flux from base to emitter: S_p
Base electrode flux: $S_p + S_n(0)-S_n(W_b)$
Gain β = collector flux /base electrode flux $= S_n(W_b)/(S_p+S_n(0)-S_n(W_b))$

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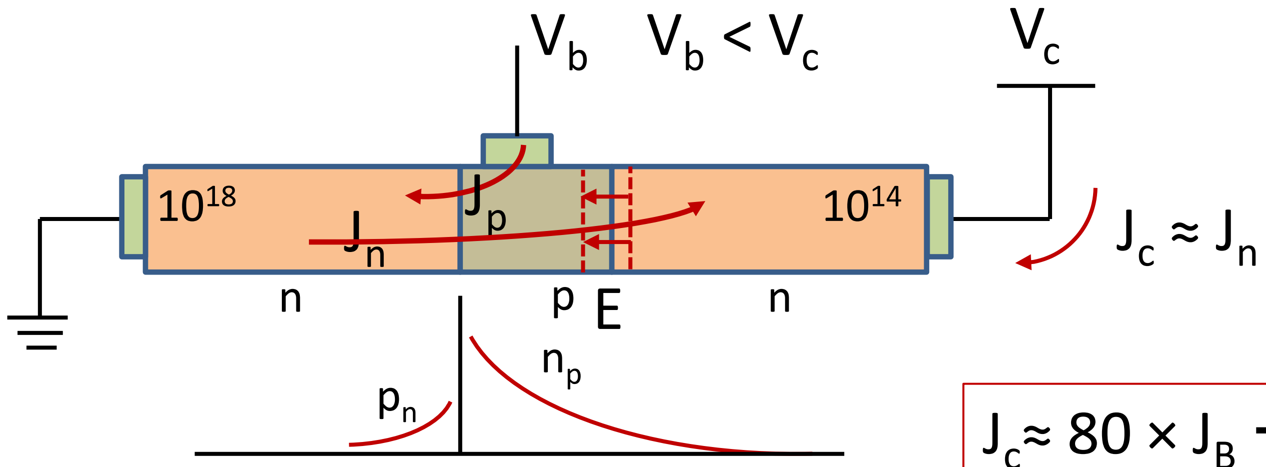

$J_c \approx 80 \times J_B \rightarrow$ Gain β=80

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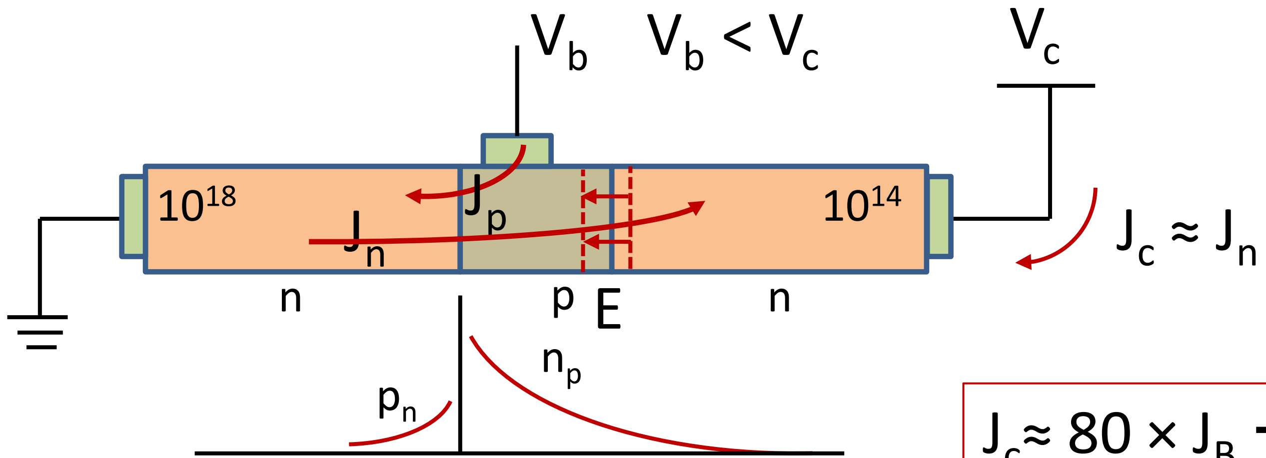

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